



RECEIVED

DEC 19 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei YAMAZAKI et al.

Art Unit : 2823

Serial No. : 09/773,543

Examiner : Neal Berezny

TECHNOLOGY CENTER 26

Filed : February 2, 2001

Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE
SAMECommissioner for Patents
Washington, D.C. 20231# 13/3
1-28-03
JewRESPONSE TO ELECTION REQUIREMENT

In response to the action mailed October 18, 2002, please amend the application as noted.

In the claims:

Please amend claims 1, 3, 4, 8, 9, 12, 13, 18, 20, 21, 23, 27, 28, 32, 33 and 37 as follows:

B1 [Handwritten notes: b1, c1, B1, Sub C1]

-- 1. (Amended) A semiconductor device comprising:
a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region, and a channel formation region interposed therebetween;
a first insulating film formed on said semiconductor layer;
at least one electrode formed on said first insulating film, and overlapping said channel formation region;
a source wiring formed on said first insulating film;
a second insulating film covering at least said at least one electrode and said source wiring; and
a gate wiring formed on said second insulating film, and connected to said at least one electrode.

B2 [Handwritten notes: Sub C1]
3. (Amended) A semiconductor device according to claim 1, wherein said at least one electrode comprises a gate electrode.

12/19/2002 WASFAW1 00000080 09773543

110.00 OP

01 FC:1251